

HIGH CURRENT APPLICATION.

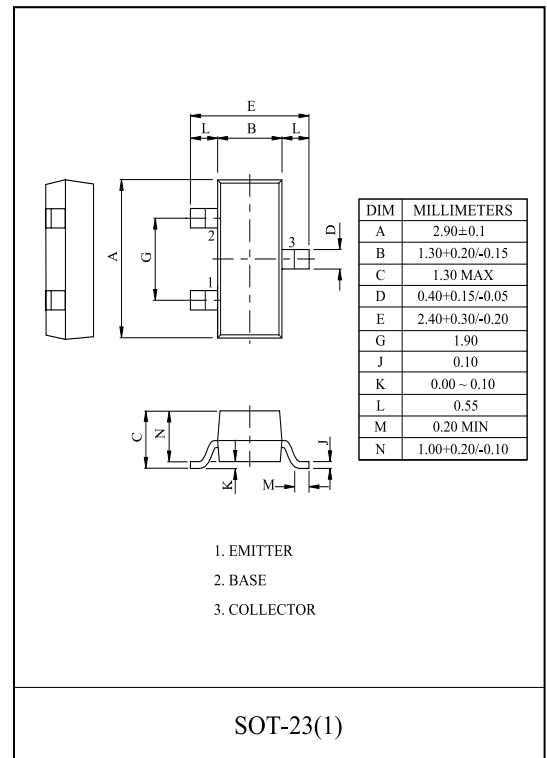
FEATURE

- Complementary to MPS8050SC.

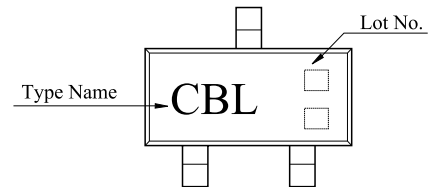
MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1,200	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

* P_C : Package Mounted On 99.5% Alumina (10 × 8 × 0.6mm)



Marking



ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-25	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -0.1mA, I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -35V, I_E = 0$	-	-	-0.1	uA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -4V, I_C = 0$	-	-	0.1	uA
DC Current Gain	h_{FE}	$V_{CE} = -1V, I_C = -100mA$	200	-	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$	-	-	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$	-	-	-1.2	V
Transition Frequency	f_T	$V_{CE} = -6V, I_C = -20mA, f = 30MHz$	150	-	-	MHz

MPS8550SC

